

Abstract of the Disclosure:

A method for fabricating embedded nonvolatile semiconductor memory cells is described. The method includes forming a first insulating layer on a substrate having a high-voltage region, a memory region and a logic region. The first insulating layer is removed in the memory region, and a second insulating layer is formed. A charge-storing layer is formed and patterned along with a third insulating layer. The first to third insulating layers and also the charge-storing layer are removed in the logic region. A fourth insulating layer is formed and a conductive control layer is formed and patterned.

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